

Docket No.: 198786US-2RE

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

IN RE APPLICATION: Mitsuhiro YANO, et al.

SERIAL NO.: 09/891,925

GAU: 2811

FILED: June 27, 2001

EXAMINER: HU, S.

FOR: SEMICONDUCTOR DEVICE AND METHOD OF FABRICATING SAME

**LETTER SUBMITTING REPLACEMENT DRAWING SHEET(S)**

COMMISSIONER FOR PATENTS  
Alexandria, VA 22313

SIR:

Responsive to the below indicated communication, the following drawing sheets are submitted herewith:

- ☒ 2 Replacement Drawing Sheets ☐ \_\_\_\_\_ New Drawing Sheets  
☐ \_\_\_\_\_ Annotated Drawing Sheets
- ☒ Official Action dated May 29, 2008  
☐ Notice of Allowance/Issue Fee dated \_\_\_\_\_  
☐ Other dated \_\_\_\_\_

The changes and/or modifications made include the following:

The original labeled element 16 under the gate layer 17 in Figure 2 is now newly labeled element 161, and is noted in the amended specification as formed of silicon oxide. Figure 8 is also herein amended to consistently refer to elements 8 and 7 and delete the original reference indicator "16".

Respectfully Submitted,

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